

1MHZ CMOS Rail-to-Rail IO Opamp with RF Filter

Features

Single-Supply Operation from +2.1V ~ +5.5V

Rail-to-Rail Input / Output

Gain-Bandwidth Product: 1MHz (Typ.)

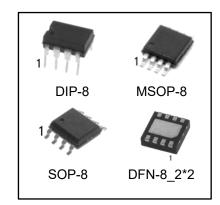
Low Input Bias Current: 1pA (Typ.)

Low Offset Voltage: 3.5mV (Max.)

Quiescent Current: 40µA per Amplifier (Typ.)

Operating Temperature: -40°C ~ +125°C

Embedded RF Anti-EMI Filter



Ordering Information

DEVICE	Package Type	MARKING	Packing	Packing Qty
LMV602PG	DIP-8	LMV602	TUBE	2000pcs/Box
LMV602DRG	SOP-8	LMV602	REEL	2500pcs/Reel
LMV602DGKRG	MSOP-8	LMV602,V602	REEL	3000pcs/Reel
LMV602DQRG	DFN-8 _2*2	LMV602	REEL	2500pcs/Reel

General Description

The LMV602 have a high gain-bandwidth product of 1MHz, a slew rate of $0.6V/\mu s$, and a quiescent current of $40\mu A/amplifier$ at 5V. The LMV602 is designed to provide optimal performance in low voltage and low noise systems. They provide rail-to-rail output swing into heavy loads. The input common mode voltage range includes ground, and the maximum input offset voltage is 3.5mV for LMV602. They are specified over the extended industrial temperature range (-40% to+125%). The operating range is from 2.1V to 5.5V. The LMV602 Dual is available in Green SOP-8, MSOP8, DIP-8 and DFN-8 packages.

Applications

- ASIC Input or Output Amplifier
- Sensor Interface
- Medical Communication
- Smoke Detectors
- Audio Output
- Piezoelectric Transducer Amplifier
- Medical Instrumentation
- Portable Systems



Pin Configuration



Figure 1. LMV602 Pin Assignment Diagram

Absolute Maximum Ratings

Condition	Min	Max			
Power Supply Voltage (V _{DD} to Vss)	-0.5V	+7.5V			
Analog Input Voltage (IN+ or IN-)	Vss-0.5V	V _{DD} +0.5V			
PDB Input Voltage	Vss-0.5V	+7V			
Operating Temperature Range	-40°C	+125°C			
Junction Temperature	+160	0°C			
Storage Temperature Range	-55°C	+150°C			
Lead Temperature (soldering, 10sec)	+24	5°C			
Package Thermal Resistance (TA=+25℃)					
SOP-8, θJA	125°	C/W			
MSOP-8, θJA	216°C/W				
ESD Susceptibility					
HBM 6KV					
MM	300)V			

Note: Stress greater than those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification are not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.



Electrical Characteristics

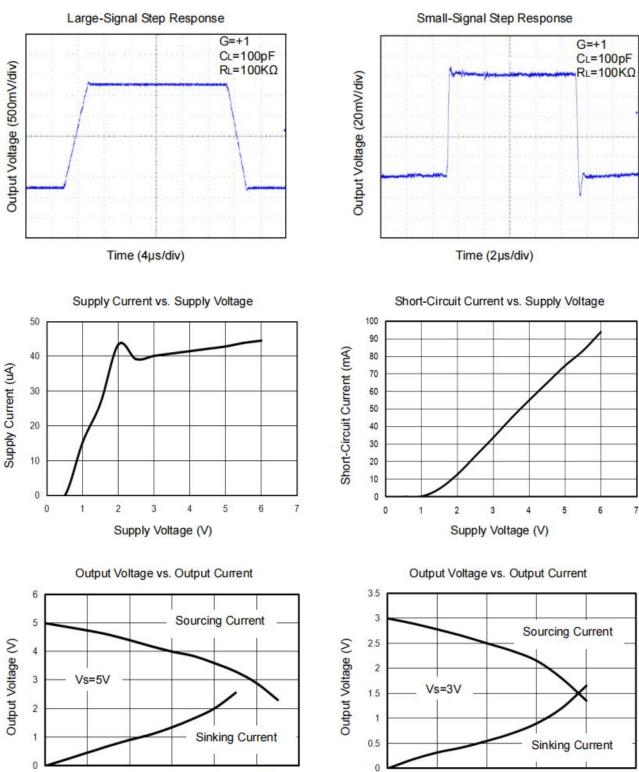
(At $V_S = +5V$, $R_L = 100k\Omega$ connected to $V_S/2$, and $V_{OUT} = V_S/2$, unless otherwise noted.)

DADAMETED	CAMBOI	CONDITIONS	TYP	MIN/MAX OVER TEMPERATURE				
PARAMETER	SYMBOL	+25		+25℃	-40℃to+85℃	UNITS	MIN/MAX	
INPUT CHARACTERISTIC	s							
Input Offset Voltage	Vos	V _{CM} = VS/2	0.4	3.5	5.6	mV	MAX	
Input Bias Current	I _B		1			pА	TYP	
Input Offset Current	los		1			pА	TYP	
Common-Mode	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	\/ - F E\/	-0.1 to			.,	7. (5)	
Voltage Range	V _{CM}	V _S = 5.5V	+5.6			V	TYP	
Common-Mode	CMRR	V_S =5.5V, V_{CM} = -0.1V to 4V	70	62	62	dB	MINI	
Rejection Ratio	CIVIRR	V _S =5.5V, V _{CM} = -0.1V to 5.6V	68	56	55		MIN	
Ones Leen Veltage Cain		$R_L=5k\Omega$, $V_O=+0.1V$ to $+4.9V$	80	70	70	dB	NAINI	
Open-Loop Voltage Gain	A _{OL}	$R_L=10k\Omega$, $V_O=+0.1V$ to +4.9V	100	90	85		MIN	
Input Offset Voltage Drift	ΔV _{OS} /Δ _T		2.7			µV/℃	TYP	
OUTPUT CHARACTERIST	ics		'					
	V _{OH}	$R_L = 100k\Omega$	4.997	4.990	4.980	V	MIN	
Output Voltage	V _{OL}	$R_L = 100k\Omega$	3	10	20	mV	MAX	
Swing from Rail	Vон	$R_L = 10k\Omega$	4.992	4.970	4.960	V	MIN	
	V _{OL}	$R_L = 10k\Omega$	8	30	40	mV	MAX	
	Isource	84		60	45			
Output Current	I _{SINK}	$R_L = 10\Omega$ to VS/2	75	60	45	mA N	MIN	
POWER SUPPLY								
				2.1	2.5	V	MIN	
Operating Voltage Range				5.5	5.5	V	MAX	
Power Supply		V _S = +2.5V to +5.5V,			_			
Rejection Ratio	PSRR	V _{CM} = +0.5V	82	60	58	dB	MIN	
Quiescent Current /								
Amplifier	lQ		40	60	80	μA	MAX	
DYNAMIC PERFORMANC	E (CL = 100	OpF)	'					
Gain-Bandwidth Product	GBP		1			MHz	TYP	
Slew Rate	SR	G = +1, 2V Output Step	0.6			V/µs	TYP	
Settling Time to 0.1%	ts	G = +1, 2V Output Step	5			μs	TYP	
Overload Recovery Time		V _{IN} ·Gain = VS	2.6			μs	TYP	
NOISE PERFORMANCE		1					1	
\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \		f = 1kHz	27			nV /√Hz	TYP	
Voltage Noise Density	e _n	f = 10kHz	20			nV/√Hz	TYP	



Typical Performance characteristics

At T_A =+25°C, V_S =+5V, and R_L =100K Ω connected to $V_S/2$, unless otherwise noted.



20

60

Output Current (mA)

80

100

50

40

120

10

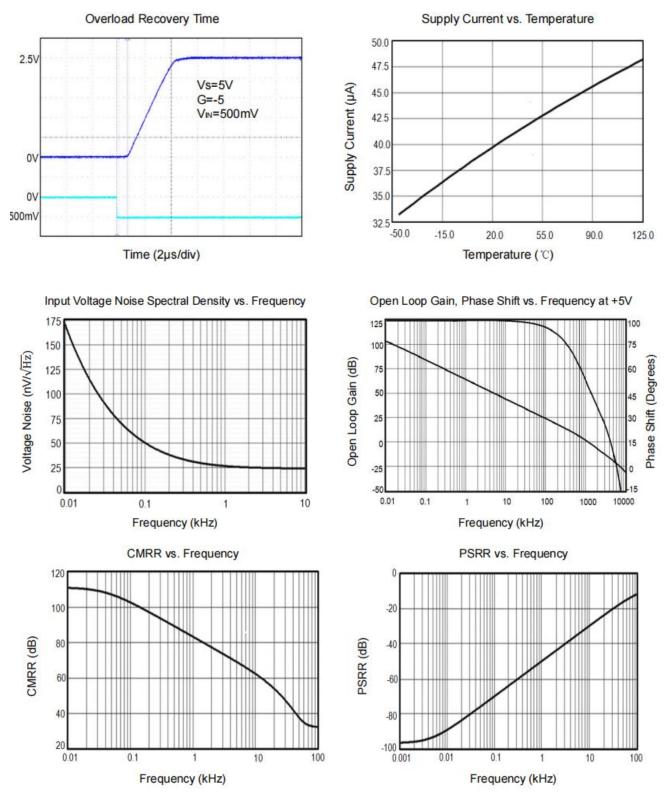
20

Output Current (mA)



Typical Performance characteristics

At T_A =+25°C, V_S =+5V, and R_L =100K Ω connected to $V_S/2$, unless otherwise noted.





Application Note

Power Supply Bypassing and Board Layout

LMV602 series operates from a single 2.1V to 5. 5V supply or dual ± 1.05 V to ± 2.75 V supplies. For best performance, a 0.1μ F ceramic capacitor should be placed close to the VDD pin in single supply operation. For dual supply operation, both V_{DD} and VSS supplies should be bypassed to ground with separate 0.1μ F ceramic capacitors.

Low Supply Current

The low supply current (typical 40uA per channel) of LMV602 will help to maximize battery life. They are ideal for battery powered systems

Operating Voltage

LMV602 operates under wide input supply voltage (2.1V to 5.5V). In addition, all temperature specifications apply from -40°C to +125°C. Most behavior remains unchanged throughout the full operating voltage range. These guarantees ensure operation throughout the single Li-lon battery lifetime

Rail-to-Rail Input

The input common-mode range of LMV602 extends 100mV beyond the supply rails (VSS-0.1V to VDD+0.1V). This is achieved by using complementary input stage. For normal operation, inputs should be limited to this range.

Rail-to-Rail Output

Rail-to-Rail output swing provides maximum possible dynamic range at the output. This is particularly important when operating in low supply voltages. The output voltage of LMV602 can typically swing to less than 5 mV from supply rail in light resistive loads (>100k Ω), and 30mV of supply rail in moderate resistive loads (10k Ω).

Capacitive Load Tolerance

The LMV602 is optimized for bandwidth and speed, not for driving capacitive loads. Output capacitance will create a pole in the amplifier's feedback path, leading to excessive peaking and potential oscillation. If dealing with load capacitance is a requirement of the application, the two strategies to consider are (1) using a small resistor in series with the amplifier's output and the load capacitance and (2) reducing the bandwidth of the amplifier's feedback loop by increasing the overall noise gain. Figure 2. shows a unity gain follower using the series resistor strategy. The resistor isolates the output from the capacitance and, more importantly, creates a zero in the feedback path that compensates for the pole created by the output capacitance.



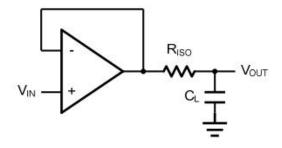


Figure 2. Indirectly Driving a Capacitive Load Using Isolation Resistor

The bigger the RISO resistor value, the more stable VOUT will be. However, if there is a resistive load RL in parallel with the capacitive load, a voltage divider (proportional to RISO/RL) is formed, this will result in a gain error.

The circuit in Figure 3 is an improvement to the one in Figure 2. RF provides the DC accuracy by feed-forward the VIN to RL. CF and RISO serve to counteract the loss of phase margin by feeding the high frequency component of the output signal back to the amplifier's inverting input, thereby preserving the phase margin in the overall feedback loop. Capacitive drive can be increased by increasing the value of CF. This in turn will slow down the pulse response.

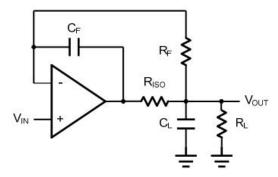
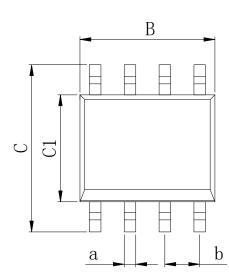


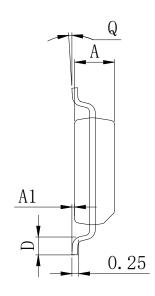
Figure 3. Indirectly Driving a Capacitive Load with DC Accuracy



Physical Dimensions

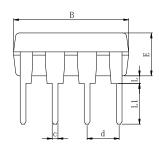
SOP-8



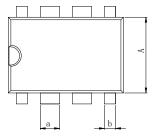


Dimensions In Millimeters(SOP-8)									
Symbol:	Α	A1	В	С	C1	D	Q	а	b
Min:	1.35	0.05	4.90	5.80	3.80	0.40	0°	0.35	1.27 BSC
Max:	1.55	0.20	5.10	6.20	4.00	0.80	8°	0.45	1.21 BSC

DIP-8





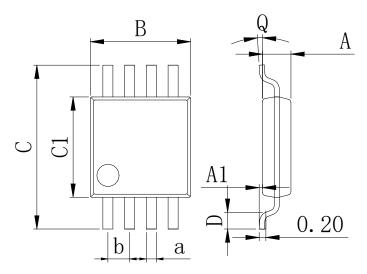


Dimensions In Millimeters(DIP-8)											
Symbol:	Α	В	D	D1	Е	L	L1	а	b	С	d
Min:	6.10	9.00	8.10	7.42	3.10	0.50	3.00	1.50	0.85	0.40	2 F4 BCC
Max:	6.68	9.50	10.9	7.82	3.55	0.70	3.60	1.55	0.90	0.50	2.54 BSC



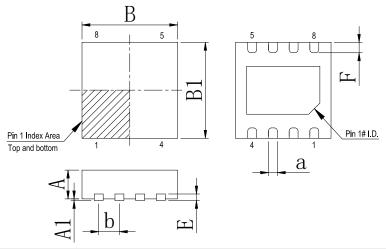
Physical Dimensions

MSOP-8



Dimensions In Millimeters(MSOP-8)									
Symbol:	А	A1	В	С	C1	D	Q	а	b
Min:	0.80	0.05	2.90	4.75	2.90	0.35	0°	0.25	0.65 BSC
Max:	0.90	0.20	3.10	5.05	3.10	0.75	8°	0.35	0.00 BSC

DFN-8 2*2



Dimensions In Millimeters(DFN-8 2*2)									
Symbol:	Α	A1	В	B1	Е	F	а	b	
Min:	0.85	0	1.90	1.90	0.15	0.25	0.18	0.50TYP	
Max:	0.95	0.05	2.10	2.10	0.25	0.45	0.30	0.5011P	



Revision History

DATE	REVISION	PAGE
2014-6-4	New	1-11
2023-8-28	Update encapsulation type、Update Lead Temperature、Updated DIP-8 dimension	1、2、8



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